

**MOTOROLA****MRF966
MRFC966
MRF967****The RF Line****N-CHANNEL DUAL-GATE GaAs
FIELD-EFFECT TRANSISTORS**

... depletion mode dual-gate transistors designed for high frequency amplifier and mixer applications.

- Excellent Receiver Front End
- Low Noise Figure — $NF = 1.2 \text{ dB}$, 1.0 GHz (Typ)
- High Power Gain — $G_D = 18 \text{ dB}$, 1.0 GHz (Typ)
- Low Reverse Transfer Capacitance — $C_{RSS} = 40 \text{ fF}$ (Typ)
- High Forward Transfer Admittance — $Y_{fs} = 20 \text{ mmhos}$ (Typ)
- Fully Characterized

N-CHANNEL**DUAL-GATE
GaAs FIELD-EFFECT
TRANSISTORS****MRFC966****MRF966****MRF967****MAXIMUM RATINGS**

Rating	Symbol	Value	Value	Value	Unit
Drain-Source Voltage	V_{DS}	10	10	10	Vdc
Gate-Source Voltage — Reverse	V_{G1S}	-8.0	-8.0	-8.0	Vdc
	V_{G2S}	-8.0	-8.0	-8.0	
Gate-Source Voltage — Forward	V_{G1S}	+1.0	+1.0	+1.0	Vdc
	V_{G2S}	+1.0	+1.0	+1.0	
Drain Current — Continuous	I_D	60	60	60	mAdc
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	350	350	350	mW
		$T_J = 125^\circ\text{C Max}$	3.5	3.5	
Storage Channel Temperature Range	T_{stg}	-65 to +125	-65 to +125	-65 to +125	°C
Junction Temperature Range	T_J	-65 to +125	-65 to +125	-65 to +125	°C

Handling and Packaging — MES devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MES devices should be observed.